Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	partially adj heavily adj doped adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 16:42
L2	10	partially adj heavily adj doped	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 18:05
L3	0	takahashi-kuminasa.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 16:44
L4	220	takahashi-kunimasa.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 17:24
L5	101	kitabatake-makoto.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 18:04
L6	249	uchida-masao.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 18:04
L7	29	Yamashita-kenya.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 18:04
L8	1	takahashi-kunimasa.inv. and (partially adj (heavily or highly) adj doped)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 17:25

L9	1	kitabatake-makoto.inv. and (partially adj (heavily or highly) adj doped)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 18:04
L10	1	uchida-masao.inv. and (partially adj (heavily or highly) adj doped)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 18:04
L11	1	Yamashita-kenya.inv. and (partially adj (heavily or highly) adj doped)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 18:04
L12	6	partially adj highly adj doped	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 18:08
L13	4	partially adj doped adj source	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 18:10
L14	0	partly adj doped adj source	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 18:10
L15	84	partly adj doped	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 18:24
L16	1131	(partly or partially) adj (implanted or diffused)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 18:25

L17	232	((partly or partially) adj (implanted or diffused)) and "257"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 18:49
L18	0	((highly or heavily) adj (partly or partially) adj (doped adj implanted or diffused)) and "257"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 18:49
L19	0	((highly or heavily) adj (partly or partially) near (doped or implanted or diffused)) and "257"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 18:50
L20	0	((highly or heavily) adj (partly or partially) adj (doped or implanted or diffused)) and "257"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 18:51
L21	20	((highly or heavily) near (partly or partially) near (doped or implanted or diffused)) and "257"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 18:59
L22	58	257/548.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 18:59
L23	71	257/550.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 19:08
L24	12	(sic or (silicon adj carbide)) adj misfet	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 19:10

L25	224	(sic or (silicon adj carbide)) adj mosfet	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 19:25
L27	1784	(sic or (silicon adj carbide)) and "257"/$.ccls. and (mosfet or misfet)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 20:28
L28	985	(sic or (silicon adj carbide)) and "438"/$.ccls. and (mosfet or misfet)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 19:27
L29	1105	438/197.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 20:30
L30	1080	438/514.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 20:31
L31	94	438/518.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 20:50
L32	1306	257/288.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/01 20:50